

AMENDMENTS TO THE CLAIMS

1-21. (canceled)

22. (currently amended) A magnetic random access memory structure comprising:

an insulating layer;

a planarized barrier layer disposed over the insulating layer;

plurality of longitudinally extending planarized conductive lines formed over ~~an insulating~~ said barrier layer ~~of a semiconductor substrate;~~

respective first magnetic layers over said conductive lines;

respective second magnetic layers over said first magnetic layers; and

a planarized conductive material layer formed between said planarized conductive lines and said barrier layer, and said first magnetic layers.

23. (previously presented) The structure of claim 22 wherein said conductive material layer is selected from the group consisting of tantalum (Ta), titanium (Ti), titanium-tungsten (TiW), titanium nitride (TiN) and chromium (Cr).

24. (previously presented) The structure of claim 22 wherein said conductive material layer is a resistive material.

25. (original) The structure of claim 22 wherein said insulating layer is selected from the group consisting of BPSG, SiO, SiO₂, Si₃N₄ and polyimide.

26. (previously presented) The structure of claim 22 wherein said conductive material layer is formed to a thickness of about 5 nm to about 20 nm.

27. (original) The structure of claim 22 wherein said conductive lines are formed in a trench formed in said substrate.

28. (currently amended) A memory device comprising:
at least one magnetic random access memory cell, said magnetic random access memory cell comprising:

an insulating layer;

a planarized barrier layer formed over the insulating layer;

a planarized conductor formed over the planarized barrier layer;

a first ferromagnetic layer formed over said ~~a first~~ planarized conductor[[,]];

a second ferromagnetic layer formed over said first ferromagnetic layer[[,]];

a nonmagnetic layer between said first and second ferromagnetic layers[[,]]; and

a planarized conductive material layer provided between said ~~first~~ planarized conductor and said planarized barrier layer, and said first ferromagnetic layer.

29. (previously presented) The device of claim 28 wherein said conductive material layer is selected from the group consisting of tantalum (Ta), titanium (Ti), titanium-tungsten (TiW), titanium nitride (TiN) and chromium (Cr).

30. (previously presented) The device of claim 28 wherein said conductive material layer is a resistive material.

31. (original) The device of claim 28 wherein said insulating layer is selected from the group consisting of BPSG, SiO, SiO₂, Si₃N₄ or polyimide.

32. (previously presented) The device of claim 28 wherein said conductive material layer is formed to a thickness of about 5 nm to about 20 nm.

33. (previously presented) The device of claim 28 wherein said planarized ~~first~~ conductor is formed in a trench of a substrate.

34-39. (canceled)

40. (new) The structure of claim 22, wherein respective first magnetic layers over said conductive lines are also over said planarized barrier layer.

41. (new) The device of claim 28, wherein the first ferromagnetic layer formed over said planarized conductor also is formed over said planarized barrier layer.